

HD74ALVCH16501

18-bit Universal Bus Transceivers with 3-state Outputs

REJ03D0036-0300Z (Previous ADE-205-168A(Z)) Rev.3.00 Oct.02.2003

Description

Data flow in each direction is controlled by output enable (OEAB and OEBA), latch enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. For A to B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CLKAB is held at a high or low logic level. If LEAB is low, the A bus data is stored in the latch flip flop on the low to high transition of CLKAB. When OEAB is high, the outputs are active. When OEAB is low, the outputs are in the high impedance state. Data flow for B to A is similar to that of A to B but uses OEBA, LEBA, and CLKBA. The output enables are complementary (OEAB is active high, and OEBA is active low). Active bus hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

Features

- $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$
- Typical V_{OL} ground bounce $< 0.8 \text{ V} (@V_{CC} = 3.3 \text{ V}, \text{Ta} = 25^{\circ}\text{C})$
- Typical V_{OH} undershoot > 2.0 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- High output current ± 24 mA (@V_{CC} = 3.0 V)
- Bus hold on data inputs eliminates the need for external pullup / pulldown resistors





Function Table *3

Inputs		Output B		
OEAB	LEAB	CLKAB	Α	
L	Х	Х	Х	Z
Н	Н	Х	L	L
Н	Н	Χ	Н	Н
Н	L		L	L
Н	L		Н	H
Н	L	Н	Х	B0 *1
Н	L	L	Х	B0 *2

H: High level

L : Low level

X: Immaterial

Z : High impedance

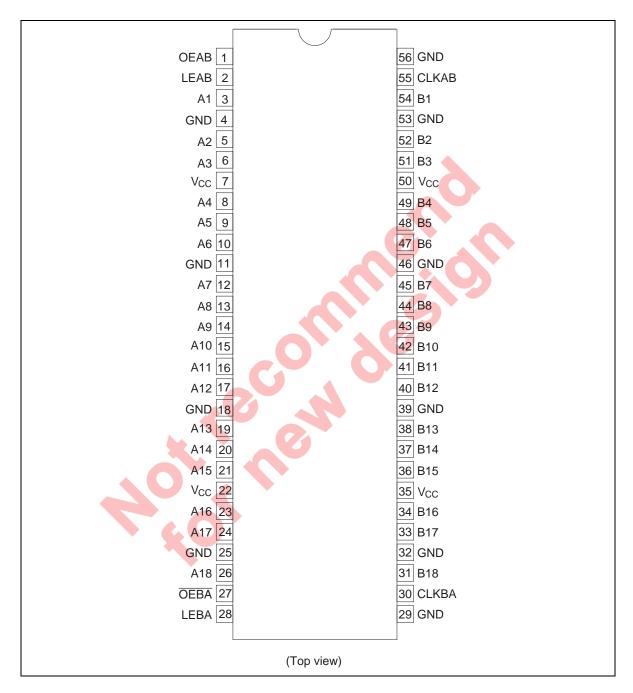
↑ : Low to high transition

Notes: 1. Output level before the indicated steady state input conditions were established.

- 2. Output level before the indicated steady state input conditions were established, provided that CLKAB was high before LEAB went low.
- 3. A to B data flow is show; B to A flow is similar but uses OEBA, LEBA, and CLKBA.



Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	Vcc	-0.5 to 4.6	V	
Input voltage *1, 2	Vı	-0.5 to 4.6	-0.5 to 4.6 V	
		-0.5 to V _{CC} +0.5	-0.5 to V _{CC} +0.5	
Output voltage *1, 2	Vo	-0.5 to V _{CC} +0.5	V	
Input clamp current	I _{IK}	– 50	mA	V _I < 0
Output clamp current	I _{OK}	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	Io	±50	mA	$V_{\rm O}$ = 0 to $V_{\rm CC}$
		±100		
Maximum power dissipation at Ta = 55°C (in still air) *3	P _T	1	W	TSSOP
Storage temperature	Tstg	-65 to 150	°C	

Notes: Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

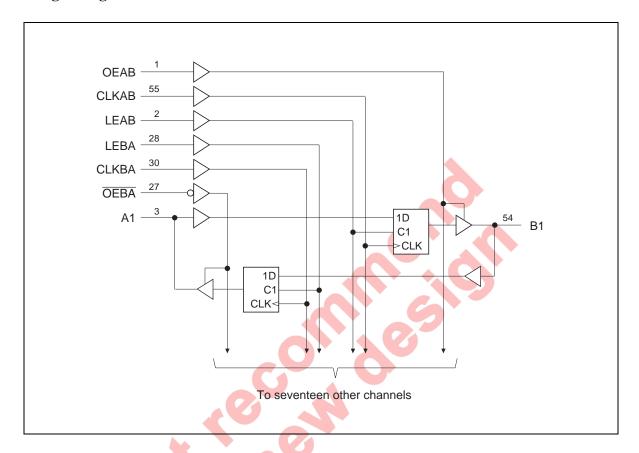
- 1. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.
- 2. This value is limited to 4.6 V maximum.
- 3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

Recommended DC Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage	Vcc	2.3	3.6	V	
Input voltage	Vı	0	V _{CC}	V	_
Output voltage	Vo	0	V _{CC}	V	
High level output current	I _{OH}	_	-12	mA	V _{CC} = 2.3 V
		_	-12	_	V _{CC} = 2.7 V
		_	-24	_	V _{CC} = 3.0 V
Low level output current	I _{OL}	_	12	mA	V _{CC} = 2.3 V
		_	12	_	V _{CC} = 2.7 V
		_	24	_	V _{CC} = 3.0 V
Input transition rise or fall rate	Δt / Δν	0	10	ns / V	
Operating temperature	Та	-40	85	°C	

Note: Unused control inputs must be held high or low to prevent them from floating.

Logic Diagram



Electrical Characteristics

 $(Ta = -40 \text{ to } 85^{\circ}C)$

Item	Symbol	V _{CC} (V) *1	Min	Max	Unit	Test Conditions
Input voltage	V _{IH}	2.3 to 2.7	1.7	_	V	
		2.7 to 3.6	2.0	_	-	
	V _{IL}	2.3 to 2.7	_	0.7	-	
		2.7 to 3.6	_	8.0	-	
Output voltage	V _{OH}	Min to Max	V _{CC} -0.2	_	V	I _{OH} = -100 μA
		2.3	2.0	_	-	$I_{OH} = -6 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		2.3	1.7	_		I _{OH} = -12 mA, V _{IH} = 1.7 V
		2.7	2.2	_		$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		3.0	2.4	- 6		$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		3.0	2.0	-		I _{OH} = -24 mA, V _{IH} = 2.0 V
	V _{OL}	Min to Max		0.2		I _{OL} = 100 μA
		2.3	- 1	0.4		$I_{OL} = 6 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		2.3	-(0.7		I _{OL} = 12 mA, V _{IL} = 0.7 V
		2.7	-1	0.4	5)	I _{OL} = 12 mA, V _{IL} = 0.8 V
		3.0	7	0.55		I _{OL} = 24 mA, V _{IL} = 0.8 V
Input current	I _{IN}	3.6	- 4	±5	μΑ	V _{IN} = V _{CC} or GND
	I _{IN (hold)}	2.3	45	_	=	V _{IN} = 0.7 V
		2.3	-45	<u> </u>	-	V _{IN} = 1.7 V
		3.0	75	_	=	V _{IN} = 0.8 V
		3.0	- 75	_	-	V _{IN} = 2.0 V
		3.6	_	±500	-	V _{IN} = 0 to 3.6 V
Off state output current *2	loz	3.6	_	±10	μΑ	V _{OUT} = V _{CC} or GND
Quiescent supply current	Icc	3.6	_	40	μΑ	$V_{IN} = V_{CC}$ or GND
	ΔI_{CC}	3.0 to 3.6	_	750	μΑ	V_{IN} = one input at (V _{CC} -0.6) V, other inputs at V _{CC} or GND

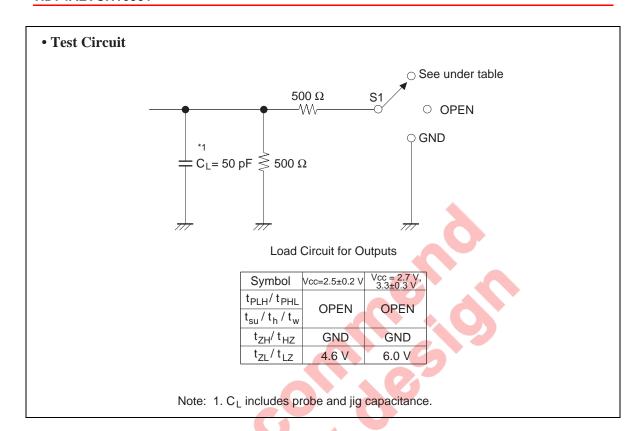
Notes: 1. For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

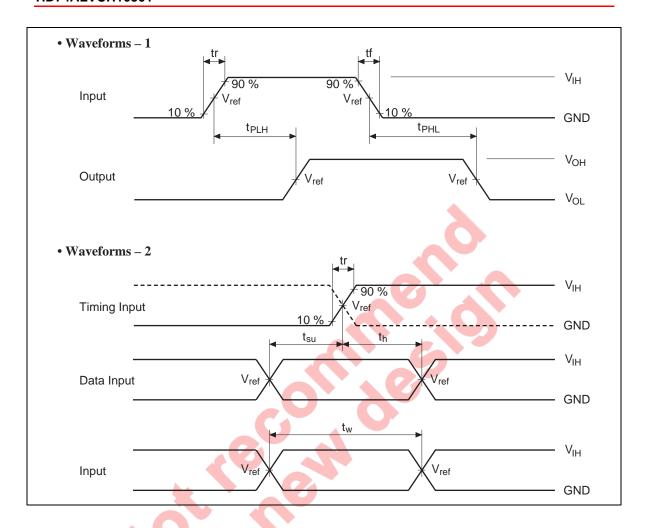
^{2.} For I/O ports, the parameter I_{OZ} includes the input leakage current.

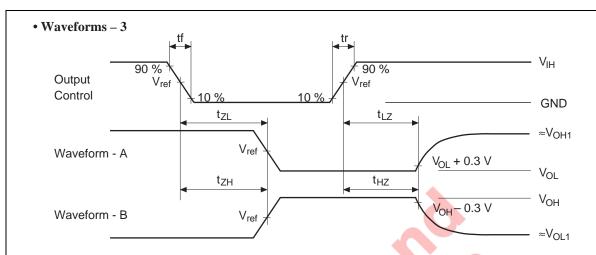
Switching Characteristics

 $(Ta = 40 \text{ to } 85^{\circ}\text{C})$

Item	Symbol	V _{CC} (V)	Min	Тур	Max	Unit	FROM (Input)	TO (Output)
Maximum clock frequency	f_{max}	2.5±0.2	150	_	_	MHz		
		2.7	150	_	_			
		3.3±0.3	150	_	_			
Propagation delay time	t _{PLH}	2.5±0.2	1.2	_	4.8	ns	A or B	B or A
	t_{PHL}	2.7	_	_	4.5			
		3.3±0.3	1.0	_	3.9	10		
		2.5±0.2	1.6	_	5.7		LE	A or B
		2.7	_	_	5.3			
		3.3±0.3	1.3	_	4.6			
		2.5±0.2	1.7	4	6.1		CLK	A or B
		2.7	_	4	5.6			
		3.3±0.3	1.4	7	4.9	7		
Output enable time	t_{ZH}	2.5±0.2	1.1	· -	5.8	ns	OEAB	В
	t_{ZL}	2.7		_	5.3			
		3.3±0.3	1.0	_ _	4.6			
		2.5±0.2	1.4		6.3		OEBA	Α
		2.7		_	6.0			
	× >	3.3±0.3	1.1	_	5.0			
Output disable time	t _{HZ}	2.5±0.2	2.2	_	6.2	ns	OEAB	В
	t _{LZ}	2.7	_	_	5.7			
		3.3±0.3	1.4	_	5.0			
		2.5±0.2	2.0	_	5.3		OEBA	Α
		2.7		_	4.6	_		
		3.3±0.3	1.3	_	4.2			
Input capacitance	C _{IN}	3.3	_	4.0	_	pF	Control in	puts
Output capacitance	C _{IN / O}	3.3	_	8.0	_	pF	A or B por	rts





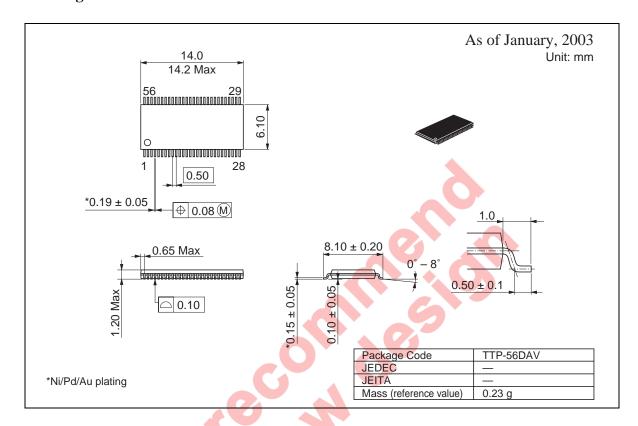


TEST	Vcc=2.5±0.2V	Vcc=2.7V, 3.3±0.3V		
V _{IH}	2.3 V	2.7 V		
V_{ref}	1.2 V	1.5 V		
V _{OH1}	2.3 V	3.0 V		
V _{OL1}	GND	GND		

Notes: 1. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Zo = 50 Ω , tr \leq 2.5 ns, tf \leq 2.5 ns.

- 2. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 3. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. The output are measured one at a time with one transition per measurement.

Package Dimensions



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